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Abstract of the Disclosure

A Si IC includes an Al-based layer (30) which is deposited as a composite of sublayers of different composition Al-based materials. In one embodiment a first sublayer (16) comprises an Al-Si-based alloy disposed so as to prevent substantial Si migration into the first sublayer (16), and a second sublayer (20), above the first (16), comprises an Al-based alloy with substantially no Si to alleviate precipitation-induced problems.

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